

Φ3mm 355nm silicon avalanche photodiode

P/N:YB-SIAPD3000UV1

❖ Applications

Laser range finder,Laser alarming,RADAR,etc. application.

❖ The features

- Top illumination planar APD
- High operation frequency,High multiplication gain

❖ Electro-Optical Characteristics (@ Tc=22±3C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Response Spectrum	λ	—	300~1100			nm
Photosensitive diameter	\emptyset	—	3000			μm
Responsivity	Re	$\lambda=355\text{nm}, \varphi_e=1\mu\text{W}, VR=10\text{V}$	—	0.22	—	A/W
		$\lambda=355\text{nm}, \varphi_e=1\mu\text{W}, VR=80\text{V}$	—	6.75	—	
Dark Current	ID	VR=0.9VBR	—	15	50	nA
Total capacitance	Ctot	VR=0.9VBR,f=1MHz	—	50	—	pF
Reverse Breakdown Voltage	VBR	IR=10uA	80		200	V
Temperature coefficient of VBR	δ	Tc=-40°C ~ 85°C	—	0.4	—	V/C

❖ The typical characteristical curve

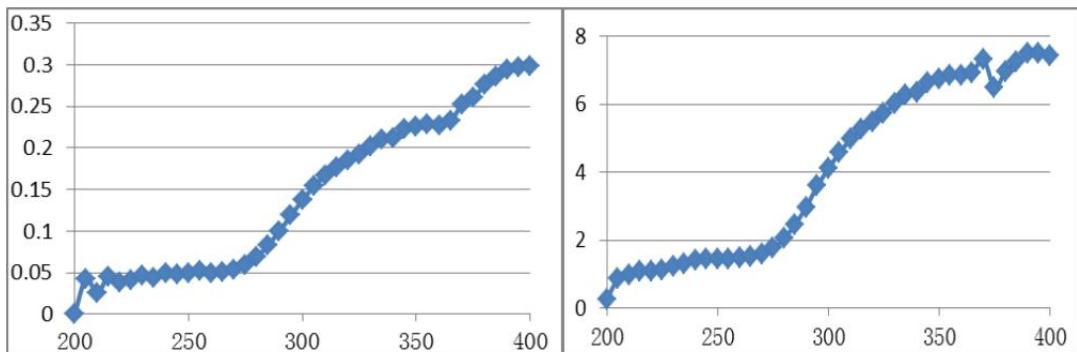


Figure1 Responsivity vs. Wavelength at 10V

Figure2 Responsivity vs. Wavelength at 80V

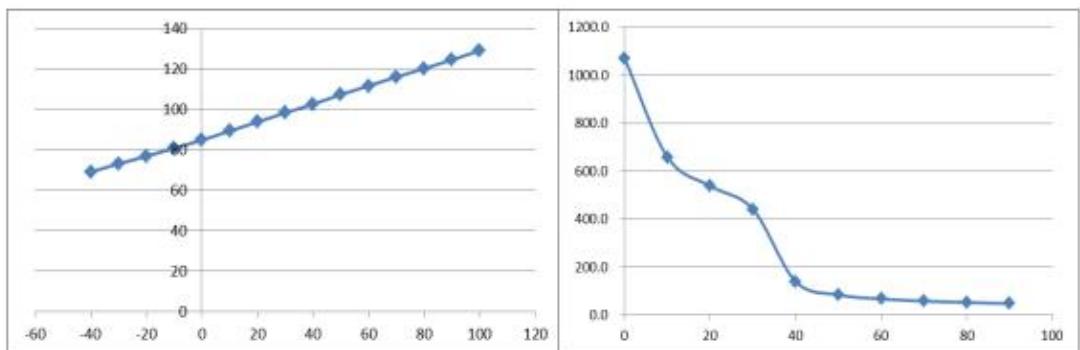
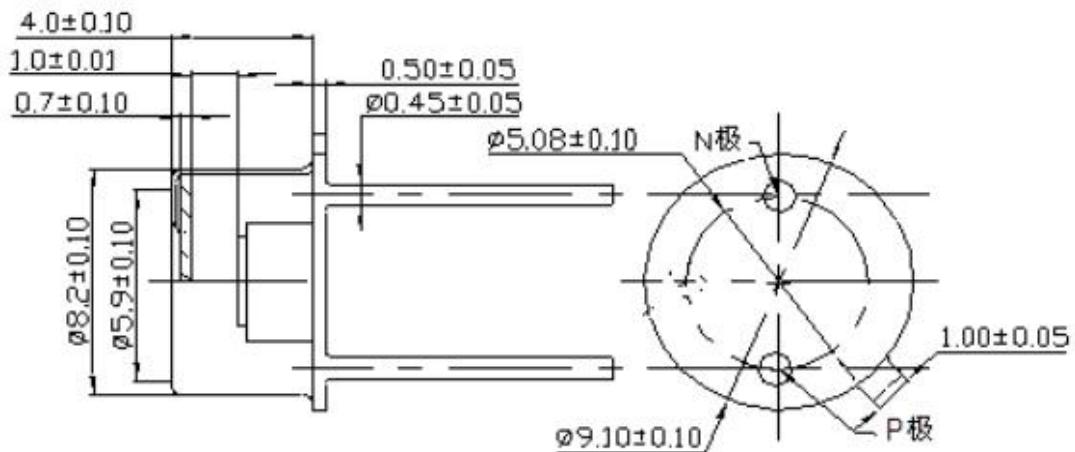


Figure3 Reverse Breakdown Voltage vs. Temperature

Figure4 Capacitance vs. Operating voltage

❖ The package and lead

Tube holder model: MBCY009-w2a



Cap Model: TO5-e

